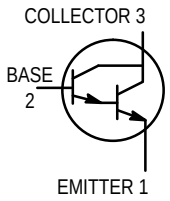
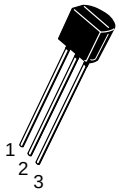
High Voltage Darlington Transistors

NPN Silicon

BC372
BC373





CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	BC372	BC373	Unit
Collector–Emitter Voltage	V_{CES}	100	80	Vdc
Collector–Base Voltage	V_{CBO}	100	80	Vdc
Emitter–Base Voltage	V_{EBO}	12		Vdc
Collector Current — Continuous	I_C	1.0		Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage(1) (I_C = 100 μAdc, I_B = 0)	 BC372 BC373	$V_{(BR)CES}$	 100 80	 — —	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	 BC372 BC373	$V_{(BR)CBO}$	 100 80	 — —	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	12	—	—	Vdc
Collector Cutoff Current (V_{CB} = 80 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0)	 BC372 BC373	I_{CBO}	 — —	 — —	 100 100	nAdc
Emitter Cutoff Current (V_{EB} = 10 V, I_C = 0)		I_{EBO}	—	—	100	nAdc

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS(1)					
DC Current Gain (I_C = 250 mAdc, V_{CE} = 5.0 Vdc) (I_C = 100 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	 8.0 10	 — —	 — 160	K
Collector–Emitter Saturation Voltage (I_C = 250 mAdc, I_B = 0.25 mAdc)	$V_{CE(sat)}$	—	1.0	1.1	Vdc
Base–Emitter Saturation Voltage (I_C = 250 mAdc, I_B = 0.25 mAdc)	$V_{BE(sat)}$	—	1.4	2.0	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain Bandwidth Product (I_C = 100 mAdc, V_{CE} = 5.0 Vdc, f = 100 MHz)	f_T	100	200	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	—	10	25	pF
Noise Figure (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc, R_g = 100 k ohm, f = 1.0 kHz)	NF	—	2.0	—	dB

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle 2.0%.

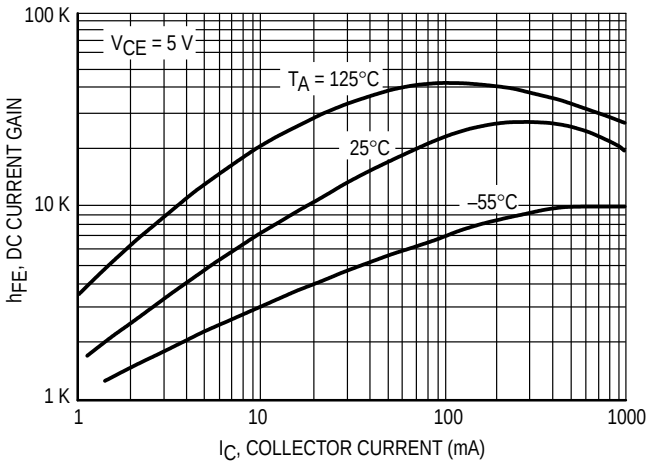


Figure 1. DC Current Gain

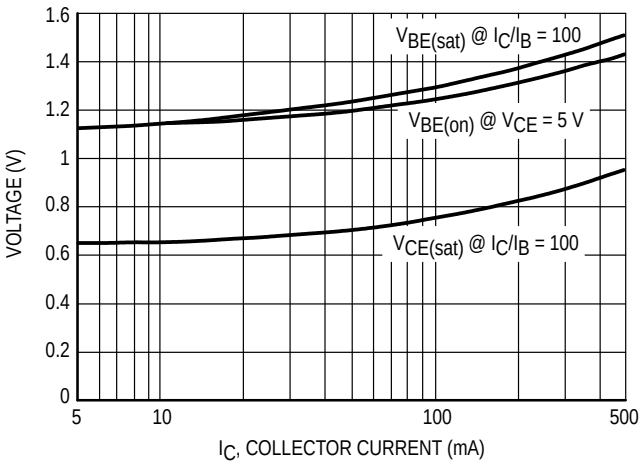


Figure 2. “Saturation” and “On” Voltages

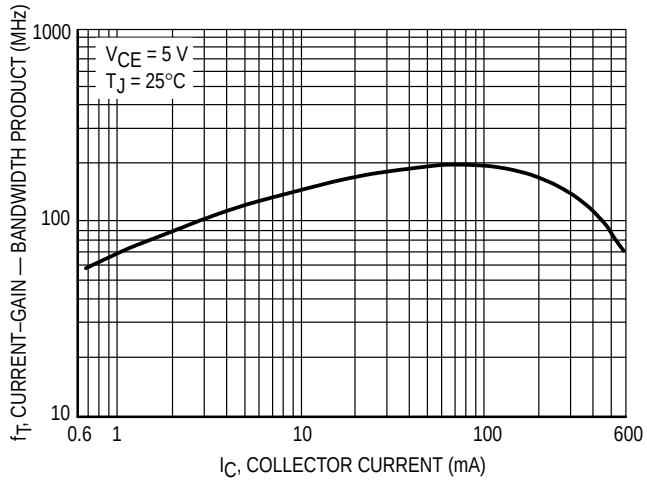


Figure 3. Current–Gain — Bandwidth Product

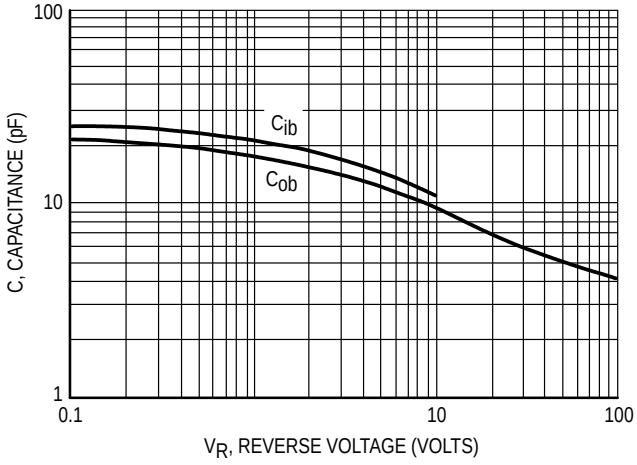
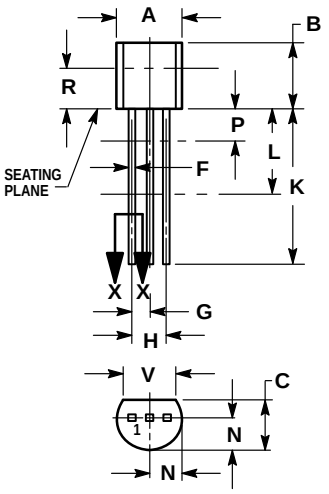
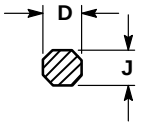


Figure 4. Capacitances

PACKAGE DIMENSIONS





SECTION X–X

CASE 029–04
(TO–226AA)
ISSUE AD

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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